

International Application No.: PCT/JP2005/004036

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IN THE ABSTRACT:

Please replace the Abstract of the Disclosure originally filed with the above-identified patent application with the following new Abstract of the Disclosure:

ABSTRACT OF THE DISCLOSURE

In a method for fabricating a semiconductor device and an apparatus for inspecting a semiconductor, laser processing is performed at different laser powers at different positions on a monitor substrate from a plurality of substrates having undergone an SPC step, to form polycrystalline silicon film over the entire area of the substrate. Thereafter, in an optimum power inspection/extraction step, the polycrystalline silicon film formed with varying film quality on the monitor substrate is inspected on inspection equipment to determine the optimum laser power. Then, in a laser processing step, the surface of the subsequent substrates having undergone the SPC step is irradiated with laser at the optimum laser power. Thus, high-quality polycrystalline silicon film is formed over the entire area of the substrate.